

TOSHIBA Photocoupler GaAlAs Ired & Photo IC

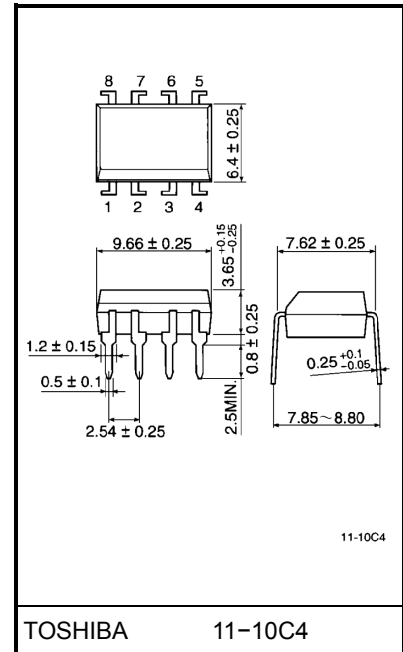
6N135, 6N136

Digital Logic Isolation.
 Line Receiver.
 Power Supply Control
 Switching Power Supply
 Transistor Inverter

The TOSHIBA 6N135 and 6N136 consists of a high emitting diode and a one chip photo diode-transistor.
 Each unit is 8-lead DIP package.

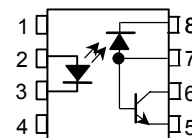
- Isolation voltage: 2500V_{rms} (min.)
- High speed: t_{pHL}, t_{pLH} = 0.5μs (typ.) (R_L = 1.9kΩ)
- TTL compatible
- If base pin is open, output signal will be noisy by environmental condition. For this base, TLP550 is suitable
- UL recognized: UL1577, file no. E67349

Unit in mm

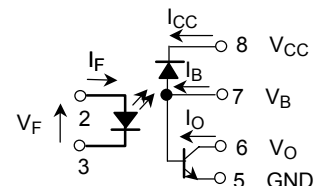


Weight: 0.54g

Pin Configurations



- 1 : N.C.
- 2 : ANODE
- 3 : CATHODE
- 4 : N.C.
- 5 : EMITTER
- 6 : COLLECTOR
- 7 : BASE, ANODE
- 8 : CATHODE



Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current (Note 1)	I_F	25	mA
	Pulse forward current (Note 2)	I_{FP}	50	mA
	Total pulse forward current (Note 3)	I_{FPT}	1	A
	Reverse voltage	V_R	5	V
	Diode power dissipation (Note 4)	P_D	45	mW
Detector	Output current	I_O	8	mA
	Peak output current	I_{OP}	16	mA
	Emitter-base reverse voltage (pin 5-7)	V_{EB}	5	V
	Supply voltage	V_{CC}	-0.5~15	V
	Output voltage	V_O	-0.5~15	V
	Base current (pin 7)	I_B	5	mA
	Output power dissipation (Note 5)	P_o	100	mW
Operating temperature range		T_{opr}	-55~100	°C
Storage temperature range		T_{stg}	-55~125	°C
Lead solder temperature (10s) (Note 6)		T_{sol}	260	°C
Isolation voltage (Note 7)		BV_S	2500	V_{rms}

(Note 1) Derate 0.8mA above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width.
Derate 1.6mA / °C above 70°C.

(Note 3) Pulse width 1μs, 300pps.

(Note 4) Derate 0.9mW / °C above 70°C.

(Note 5) Derate 2mW / °C above 70°C.

(Note 6) Soldering portion of lead: Up to 2mm from the body of the device.

(Note 7) R.H. ≤ 60%, AC / 1min.

Electrical Characteristics Over Recommended Temperature (Ta = 0°C~70°C unless otherwise noted)

Characteristic		Symbol	Test Condition	Min.	(**)Typ.	Max.	Unit	
Current transfer ratio	6N135	CTR	$I_F = 16\text{mA}, V_O = 0.4\text{V}$ $V_{CC} = 4.5\text{V}, T_a = 25^\circ\text{C}$ (Note 8)	7	18	—	%	
	6N136			19	24	—	%	
	6N135	CTR	$I_F = 16\text{mA}, V_O = 0.5\text{V}$ $V_{CC} = 4.5\text{V}$ (Note 1)	5	13	—	%	
	6N136			15	21	—	%	
Logic low output voltage	6N135	VOL	$I_F = 16\text{mA}, I_O = 1.1\text{mA}$ $V_{CC} = 4.5\text{V}$	—	0.1	0.4	V	
	6N136		$I_F = 16\text{mA}, I_O = 2.4\text{mA}$ $V_{CC} = 4.5\text{V}$	—	0.1	0.4	V	
Logic high output current			IOH	$I_F = 0\text{mA}, V_O = V_{CC} = 5.5\text{V}$ $T_a = 25^\circ\text{C}$	—	3	500	nA
				$I_F = 0\text{mA}, V_O = V_{CC} = 15\text{V}$ $T_a = 25^\circ\text{C}$	—	0.1	1	μA
			IOH	$I_F = 0\text{mA}, V_O = V_{CC} = 15\text{V}$	—	—	50	μA
Logic low supply current			ICCL	$I_F = 16\text{mA}, V_O = \text{open}$ $V_{CC} = 15\text{V}$	—	40	—	μA
Logic high supply current			ICCH	$I_F = 0\text{mA}, V_O = \text{open}$ $V_{CC} = 15\text{V}, T_a = 25^\circ\text{C}$	—	0.01	1	μA
			ICCH	$I_F = 0\text{mA}, V_O = \text{open}$ $V_{CC} = 15\text{V}$	—	—	2	μA
Input forward voltage			VF	$I_F = 16\text{mA}, T_a = 25^\circ\text{C}$	—	1.65	1.7	V
Temperature coefficient of forward voltage			$\Delta V_F / \Delta T_a$	$I_F = 16\text{mA}$	—	-1.9	—	mV / °C
Input reverse breakdown voltage			BVR	$I_R = 10\mu\text{A}, T_a = 25^\circ\text{C}$	5	—	—	V
Input capacitance			CIN	$f = 1\text{MHz}, V_F = 0$	—	60	—	pF
Resistance (input-output)			RI-O	$V_{I-O} = 500\text{V}$ R.H. ≤ 60% (Note 9)	—	10^{12}	—	Ω
Capacitance (input-output)			CI-O	$f = 1\text{MHz}$ (Note 9)	—	0.6	—	pF
Transistor DC current gain			hFE	$V_O = 5\text{V}, I_O = 3\text{mA}$	—	80	—	—

(**) All typicals at Ta = 25°C

Switching Specifications

(unless otherwise specified. $T_a = 25^\circ\text{C}$, $V_{CC} = 5\text{V}$, $I_F = 16\text{mA}$)

Characteristic	Symbol	Test Circuit	Test Condition	Min.	Typ.	Max.	Unit	
Propagation delay time to logic low at output	6N135	t_{pHL}	1	$R_L = 4.1\text{k}\Omega$	—	0.2	1.5	μs
	6N136			$R_L = 1.9\text{k}\Omega$	—	0.2	0.8	μs
Propagation delay time to logic high at output	6N135	t_{pLH}	1	$R_L = 4.1\text{k}\Omega$	—	1.0	1.5	μs
	6N136			$R_L = 1.9\text{k}\Omega$	—	0.5	0.8	μs
Common mode transient immunity at logic high level output (Note 10)	6N135	CM_H	2	$I_F = 0\text{mA}$ $V_{CM} = 10V_{p-p}$ $R_L = 4.1\text{k}\Omega$	—	1000	—	$V / \mu\text{s}$
	6N136			$I_F = 0\text{mA}$ $V_{CM} = 10V_{p-p}$ $R_L = 1.9\text{k}\Omega$	—	1000	—	$V / \mu\text{s}$
Common mode transient immunity at logic low level output (Note 10)	6N135	CM_L	2	$V_{CM} = 10V_{p-p}$ $R_L = 4.1\text{k}\Omega$ $I_F = 16\text{mA}$	—	-1000	—	$V / \mu\text{s}$
	6N136			$V_{CM} = 10V_{p-p}$ $R_L = 1.9\text{k}\Omega$ $I_F = 16\text{mA}$	—	-1000	—	$V / \mu\text{s}$
Bandwidth (Note 11)	BW	—	$R_L = 100\Omega$	—	2	—	MHz	

(Note 8) DC current transfer ratio is defined as the ratio of output collector current, I_O , to the forward LED input current, I_F , times 100%.

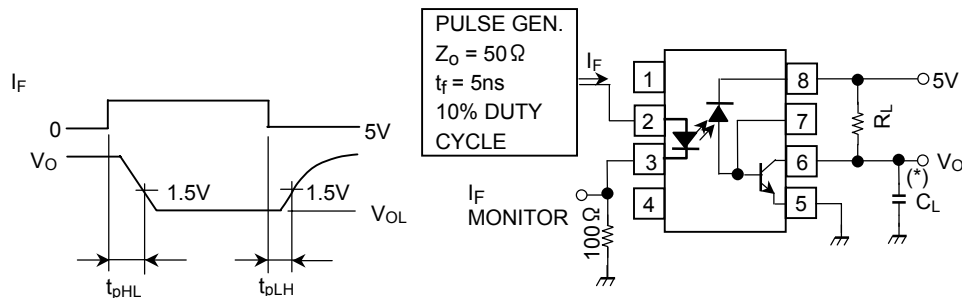
(Note 9) Device considered a two-terminal device: Pins 1, 2, 3, and 4 shorted together and pins 5, 6, 7 and 8 shorted together.

(Note 10) Common mode transient immunity in logic high level is the maximum tolerable (positive) dV_{CM} / dt on the leading edge of the common mode pulse, V_{CM} , to assure that the output will remain in a logic high state (i.e., $V_O > 2.0\text{V}$).

Common mode transient immunity in logic low level is the maximum tolerable (negative) dV_{CM} / dt on the trailing edge of the common mode pulse signal, V_{CM} , to assure that the output will remain in a logic low state (i.e., $V_O < 0.8\text{V}$).

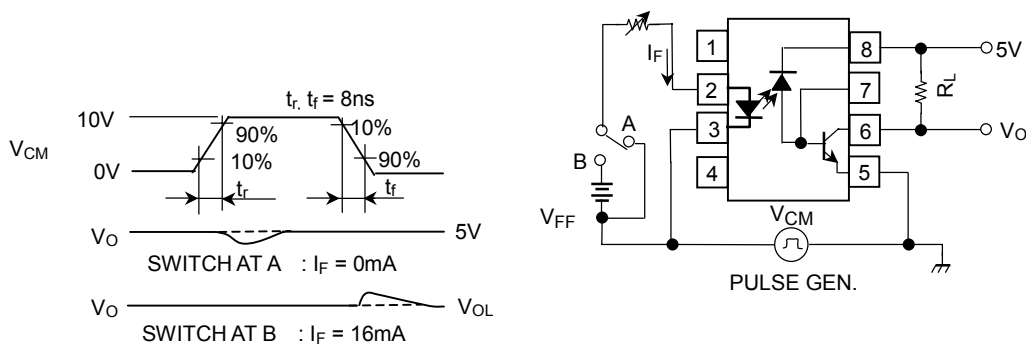
(Note 11) The frequency at which the AC output voltage is 3dB below the low frequency asymptote.

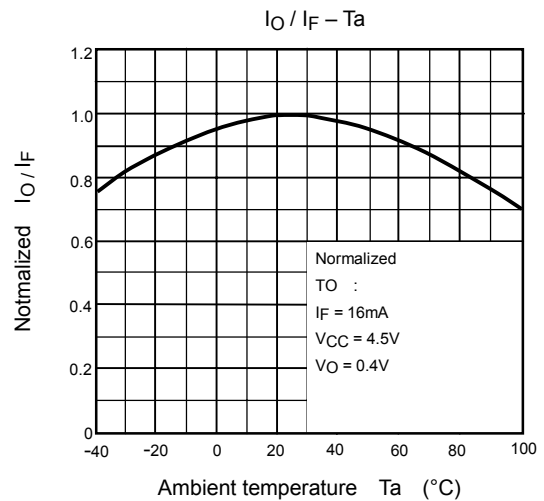
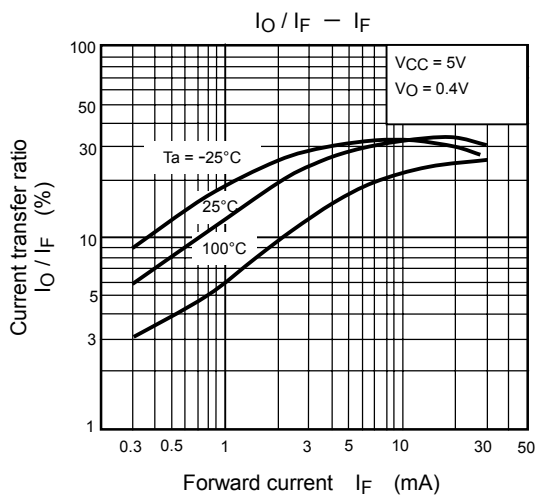
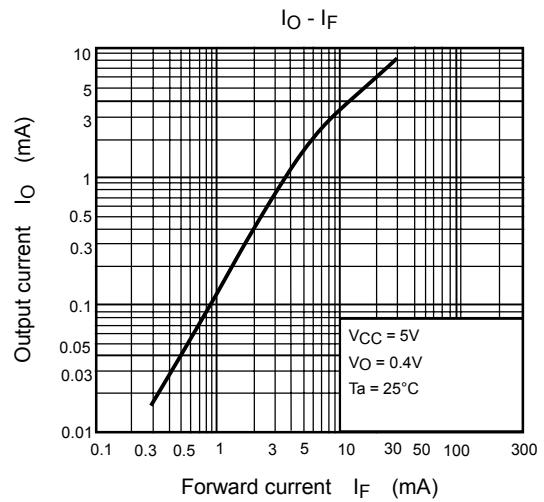
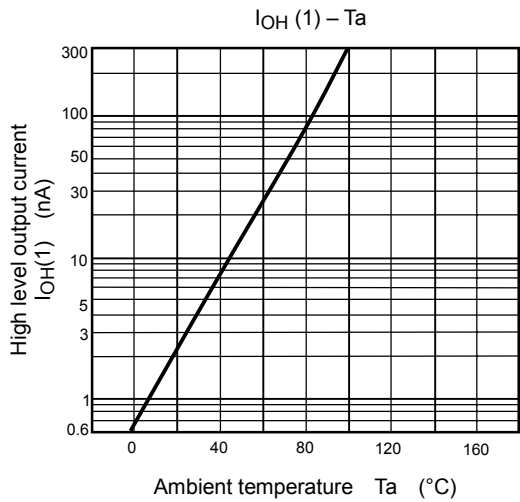
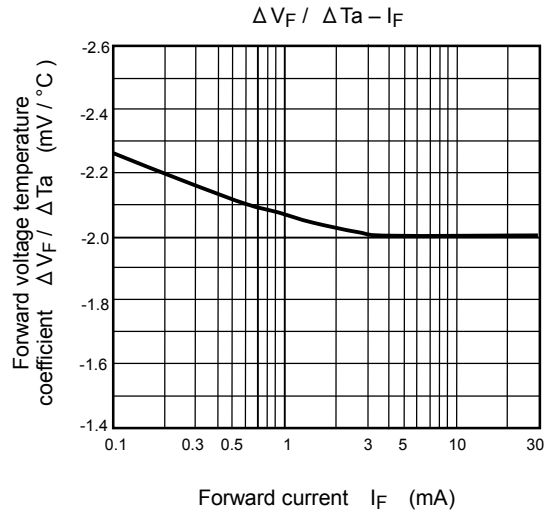
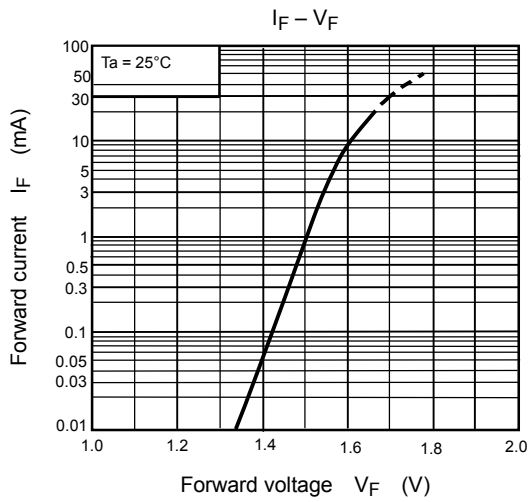
Test Circuit 1.

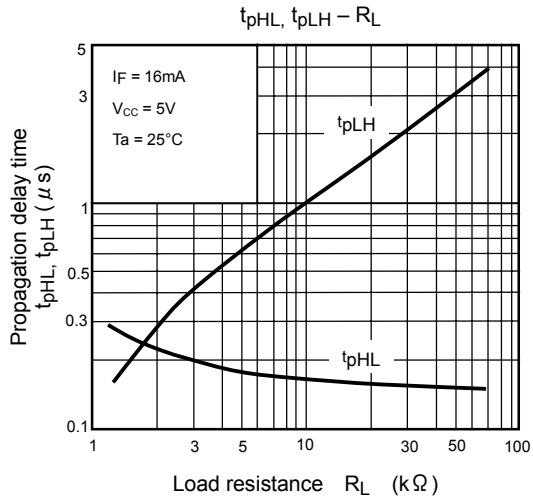
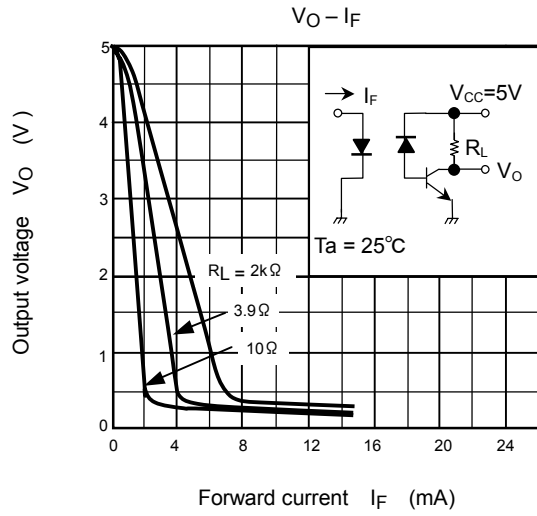
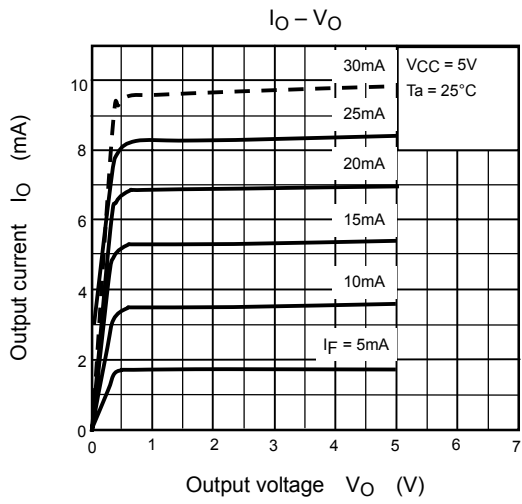


(*) C_L is approximately 15pF which includes probe and stray wiring capacitance.

Test Circuit 2.







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